BRP100N245P6

N-channel Enhancement Mode Power MOSFET

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FEATURES

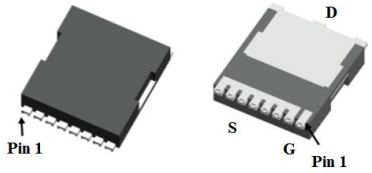
- 100V, 245A

  $R_{DS(ON)}$ < 1.2mΩ @ VGS = 10V
- Ultra-low $R_{DS(ON)}$
- Low Gate Charge
- Lead Free

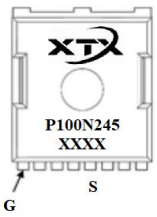
APPLICATIONS

- Motor Driving in Power Tool, E-vehicle, Robotics
- Current Switching in DC/DC & AC/DC
- Power Management

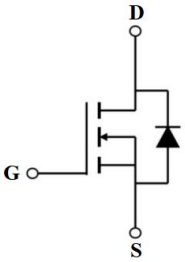
RoHS



TOLL-8



Marking and Pin Assignment



Schematic Diagram

PACKAGE MARKING AND ORDERING INFORMATION

OPN	Marking	Package	Quantity
BRP100N245P6	P100N245	TOLL-8	2000pcs/Reel

ABSOLUTE MAXIMUM RATINGS

Symbol	Definition		Ratings	Unit
V_{DS}	Drain-to-Source Voltage		100	V
V_{GS}	Gate-to-Source Voltage		±20	V
I_D	Continuous Drain Current	T_C = 25°C	245	A
		T_C = 100°C	175	A
I_{DM}	Pulsed Drain Current (1)		980	A
E_{AS}	Single Pulsed Avalanche Energy (2)		1488	mJ
P_D	Power Dissipation, T_C = 25°C		465	W
$R_{\theta JC}$	Thermal Resistance, Junction to Case		0.27	°C/W
T_J, T_{STG}	Junction & Storage Temperature Range		-55 ~ +150	°C

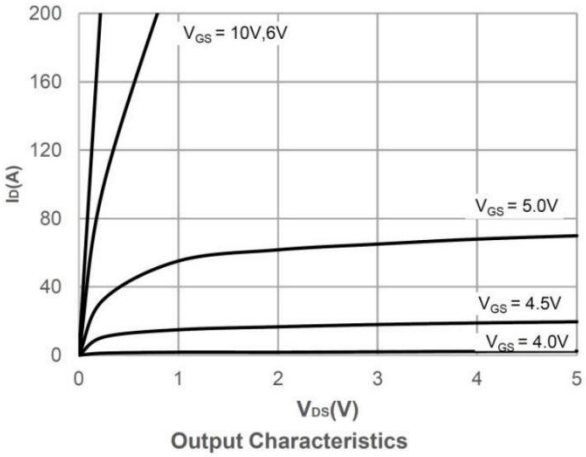
ELECTRICAL CHARACTERISTICS（All test condition is T_J=25°C, unless otherwise noted）

Symbol	Parameter	Condition	Min	Typ	Max	Unit
Off Characteristics						
$V_{(BR)DSS}$	Drain-Source Breakdown Voltage	I_D = 250μA, V_{GS} = 0V	100	-	-	V
I_{DSS}	Zero Gate Voltage Drain Current	V_{DS} = 80V, V_{GS} = 0V	-	-	1	uA
I_{GSS}	Gate-Body Leakage Current	V_{DS} = 0V, V_{GS} = ±20V	-	-	±100	nA
On Characteristics						
$V_{GS(TH)}$	Gate Threshold Voltage	V_{DS} = V_{GS}, I_D = 250uA	2.0	3.0	4.0	V
$R_{DS(ON)}$	Static Drain-Source ON-Resistance(3)	V_{GS} = 10V, I_D = 20A		1.0	1.2	mΩ
Dynamic Characteristics						
C_{iss}	Input Capacitance	V_{GS} = 0V, V_{DS} = 50V, f = 1MHz	13731	13883	14678	pF
C_{oss}	Output Capacitance		7784	8005	8209	pF
C_{rss}	Reverse Transfer Capacitance		593	722	888	pF
R_g	Gate Resistance	V_{GS} = 0V, V_{DS} = 0V, f = 1MHz	-	4.3	-	Ω
Q_g	Total Gate Charge	V_{GS} = 0 to 10V V_{DS} = 50V, I_D = 20A	-	218	-	nC
Q_{gs}	Gate Source Charge		-	66	-	nC
Q_{gd}	Gate Drain("Miller") Charge		-	57	-	nC
Switching Characteristics						
$t_{d(on)}$	Turn-On Delay Time	V_{GS} = 10V, V_{DS} = 50V I_D = 20A, R_{GEN} = 1.6Ω	-	43	-	ns
t_r	Turn-On Rise Time		-	71	-	ns
$t_{d(off)}$	Turn-Off Delay Time		-	149	-	ns
t_f	Turn-Off Fall Time		-	89	-	ns
Drain-Source Diode Characteristics						
I_S	Continuous Source Current		-	-	245	A
V_{SD}	Forward on voltage	V_{GS} = 0V, I_S = 1A	-	-	1.2	V
T_{rr}	Reverse Recovery Time	I_F = 20A, di/dt = 100A/us	-	136	-	ns
Q_{rr}	Reverse Recovery Charge		-	380	-	nC

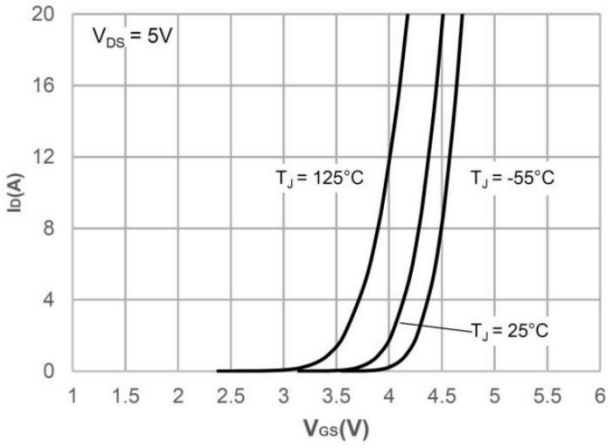
Notes:

1. Repetitive Rating: Pulse Width Limited by Maximum Junction Temperature.
2. E_{AS} condition: Starting T_J=25°C, V_{DD}=50V, V_G=10V, L=3mH, I_{AS}=31.5A
3. Pulse Test: Pulse Width ≤ 300μs, Duty Cycle ≤ 0.5%.

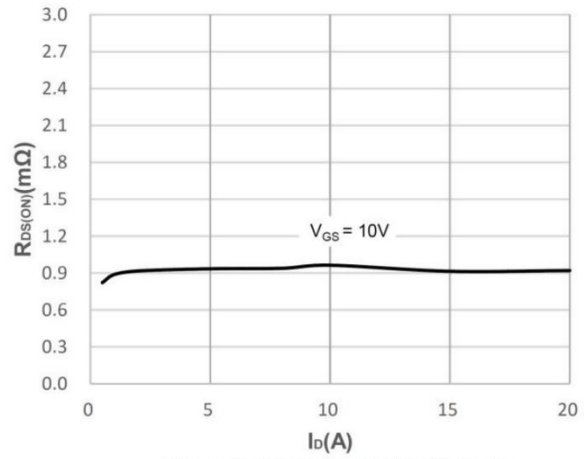
TYPICAL PERFORMANCE CHARACTERISTICS



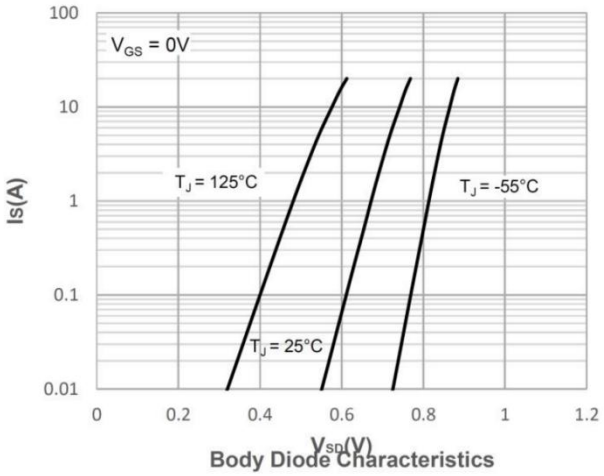
Output Characteristics



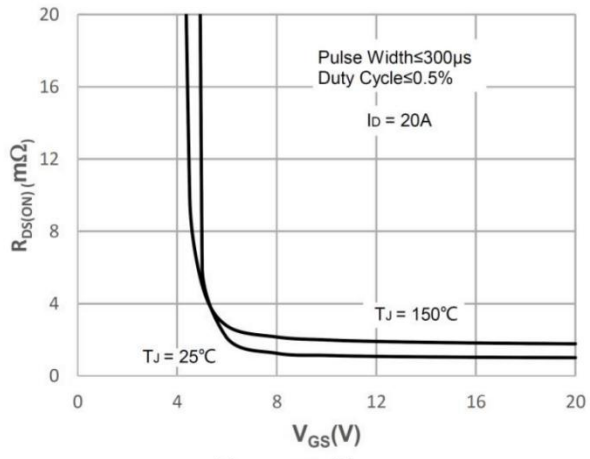
Typical Transfer Characteristics



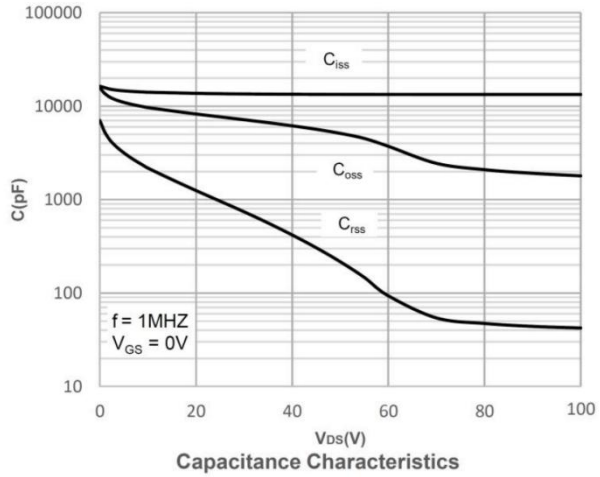
On-resistance vs. Drain Current



Body Diode Characteristics

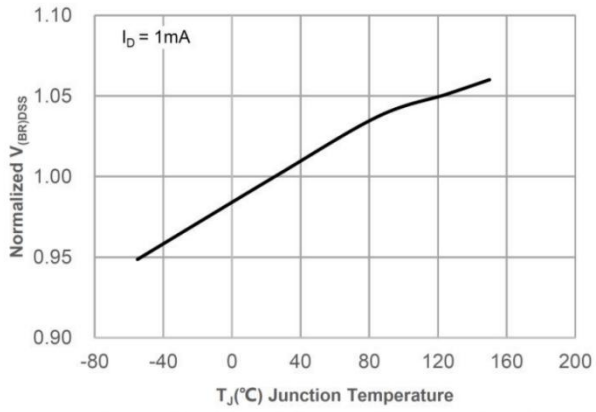


$R_{DS(ON)}$ vs. V_{GS}

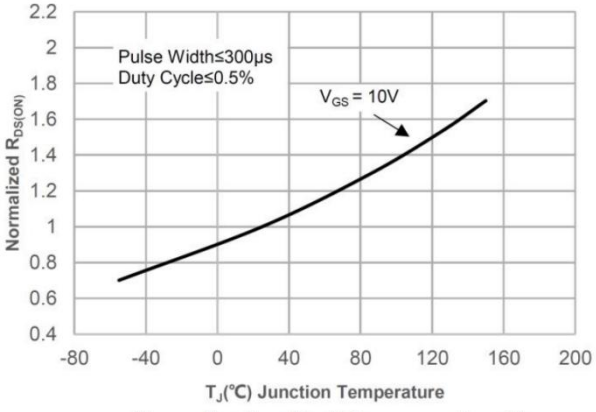


Capacitance Characteristics

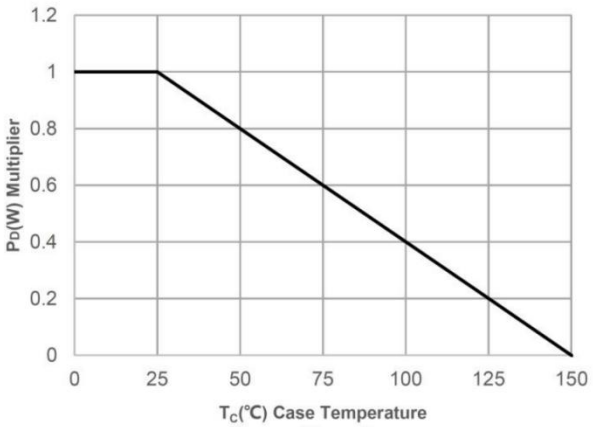
TYPICAL PERFORMANCE CHARACTERISTICS



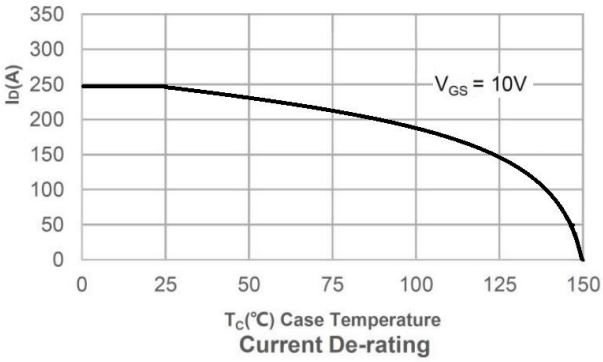
Normalized Breakdown voltage vs. Junction Temperature



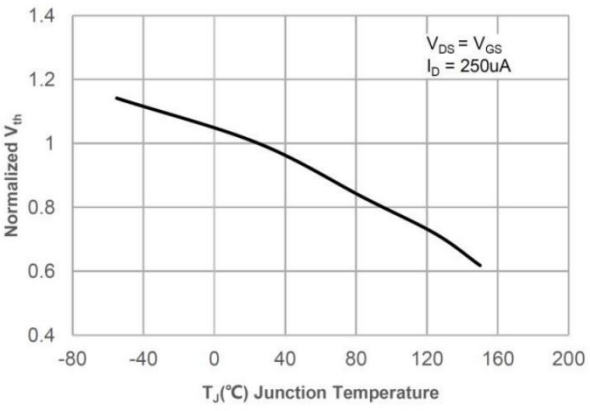
Normalized on Resistance vs. Junction Temperature



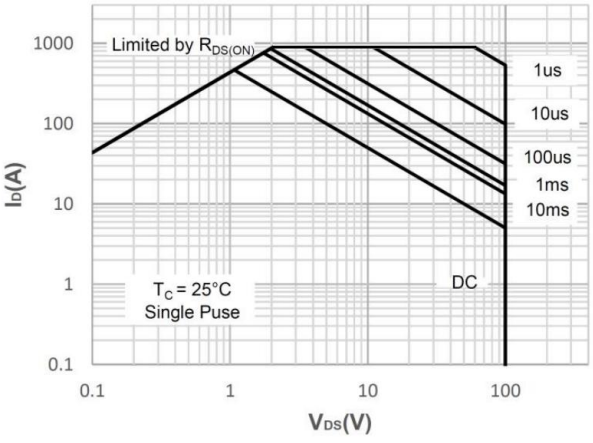
Power De-rating



Current De-rating

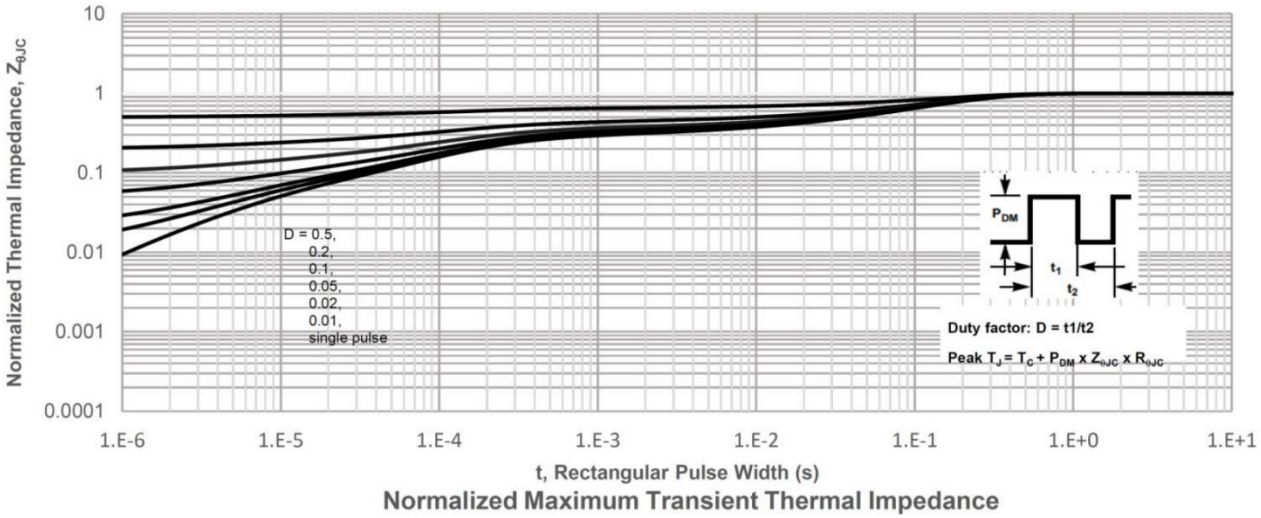


Normalized Threshold Voltage vs. Junction Temperature



Maximum Safe Operating Area

TYPICAL PERFORMANCE CHARACTERISTICS



Normalized Maximum Transient Thermal Impedance

TEST CIRCUIT

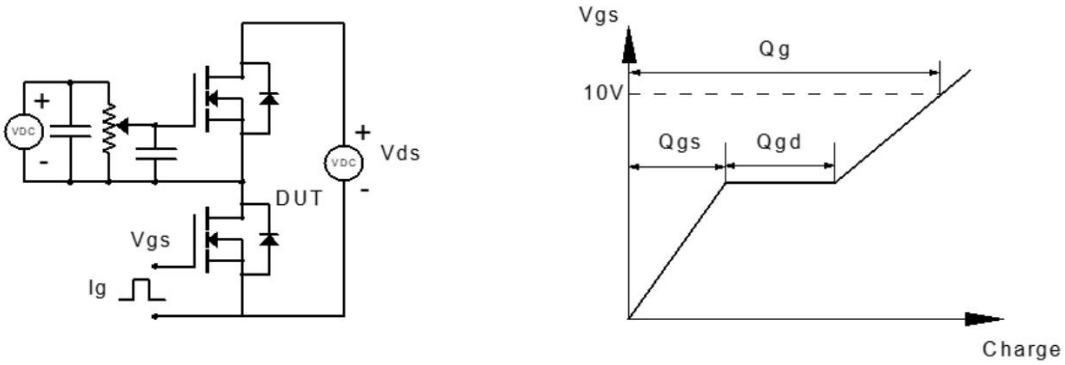


Figure 1: Gate Charge Test Circuit & Waveform

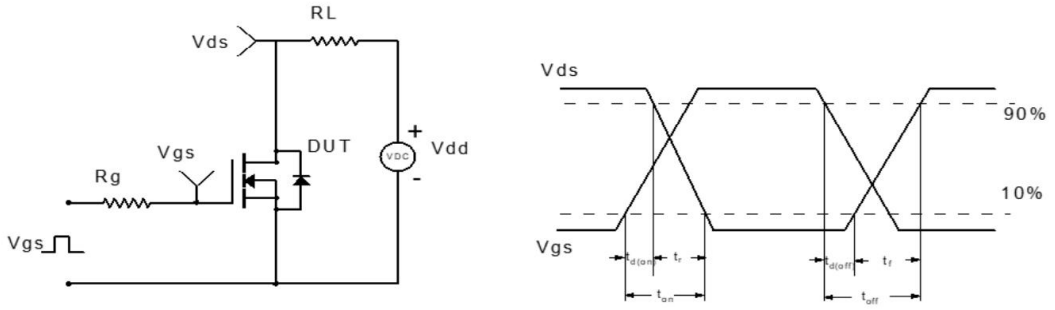


Figure 2: Resistive Switching Test Circuit & Waveform

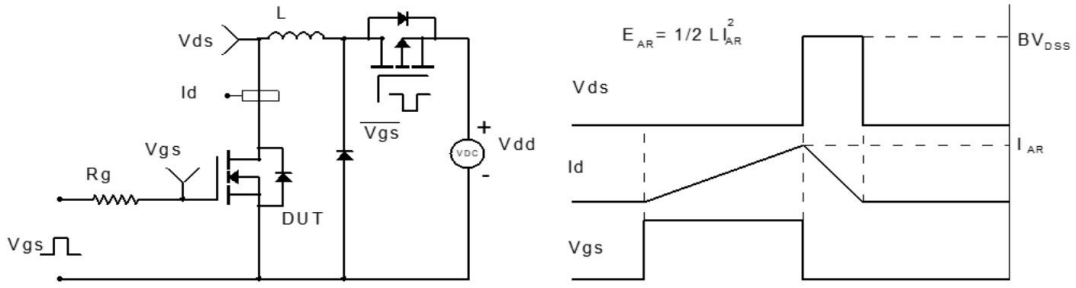


Figure 3: Unclamped Inductive Switching Test Circuit & Waveform

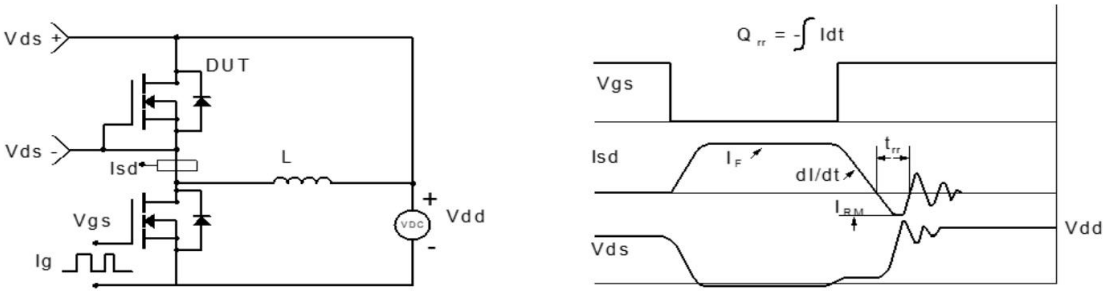
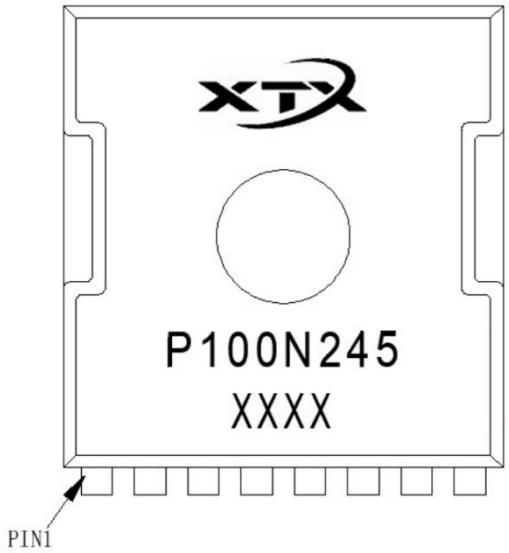


Figure 4: Diode Recovery Test Circuit & Waveform

MARKING INFORMATION



1st Line: XTX Logo

2nd Line: Part Number（P100N245）

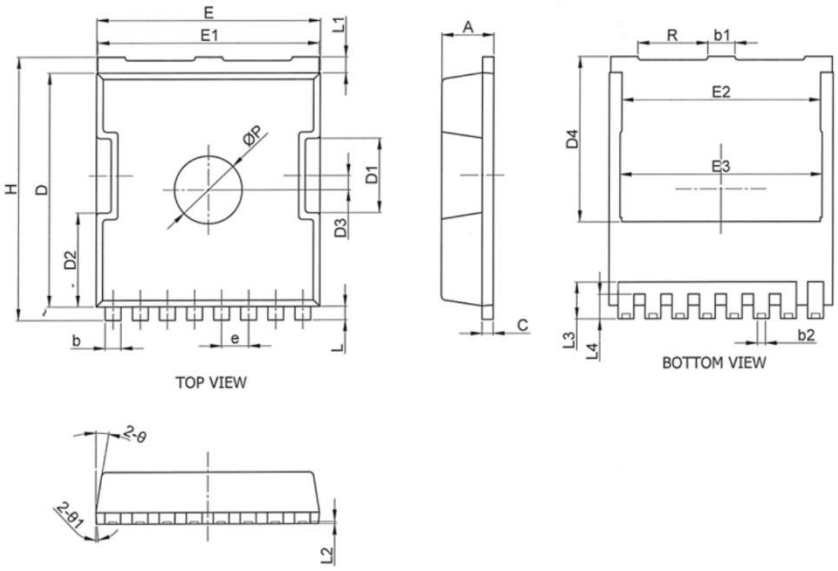
3rd Line: Date Code （XXXX）

XX: Year

XX: Week（01 to 53）

Year	2021	2022	2023	2024	2025	2026	2027	2028	2029	2030	2031	2032	2033
Code	21	22	23	24	25	26	27	28	29	30	31	32	33

DETAIL PACKAGE OUTLINE DRAWING（TOLL-8）



SYMBOL	MILLIMETERS		
	MIN	NOM	MAX
A	2.20	2.30	2.40
b	0.60	0.70	0.80
b1	1.10	1.20	1.30
b2	0.26	0.36	0.51
C	0.40	0.50	0.60
D	10.30	10.40	10.50
D1	3.20	3.30	3.40
D2	4.08	4.18	4.28
D3	0.53	0.63	0.73
D4	7.25	7.35	7.50
E	9.80	9.90	10.00
E1	9.70	9.80	9.90
E2	8.70	8.80	8.90
E3	8.85	8.95	9.05
e	1.20 BSC		
H	11.50	11.70	11.90
L	0.50	0.60	0.70
L1	0.60	0.70	0.80
L2	0.05	0.10	0.20
L3	1.45	1.65	1.85
L4	0.90	1.10	1.30
P	2.00	3.00	4.00
R	3.00	3.10	3.20
θ	7°	9°	11°
θ1	3°	5°	7°

REVISION HISTORY

Number	Description
Rev 1.0	BRP100N245P6 datasheet release